UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO. : 6,838,122 B2 DATED : January 4, 2005

INVENTOR(S) : Basceri et al.

Page 1 of 3

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page,

Item [56], References Cited, U.S. PATENT DOCUMENTS, insert the following:

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PATENT NO. : 6,838,122 B2 DATED : January 4, 200

DATED : January 4, 2005 INVENTOR(S) : Basceri et al.

Page 2 of 3

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page (cont'd),

FOREIGN PATENT DOCUMENTS, insert the following:

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UNITED STATES PATENT AND TRADEMARK OFFICE **CERTIFICATE OF CORRECTION**

PATENT NO.

: 6,838,122 B2

Page 3 of 3

DATED INVENTOR(S) : Basceri et al.

: January 4, 2005

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page (cont'd),

OTHER DOCUMENTS, insert the following:

-- Aoyama et al., Leakage Current Mechanism of Amorphous and Polycrystalline Ta2O5 Films Grown by Chemical Vapor Deposition, 143 J. ELECTROCHEM SOC., No. 3, pp 977-983 (March 1996).

Stemmer et al., Accommodation of nonstoichiometry in (100) fiber-textured (BaxSr1-x)Ti1+yO3+z thin films grown by chemical vapor deposition, 74 APPL. PHYS. LETT., No. 17, pp. 2432-2434 (26 April 1999).

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Signed and Sealed this

Eighth Day of November, 2005

JON W. DUDAS Director of the United States Patent and Trademark Office